



# THE DATASHEET OF IRFB61N15DPBF



**SMPS MOSFET**

**IRFB61N15DPbF**

HEXFET® Power MOSFET

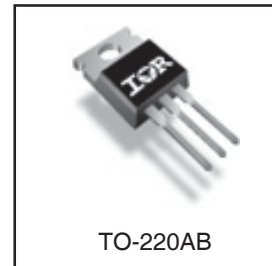
**Applications**

- High frequency DC-DC converters
- Motor Control
- Uninterruptible Power Supplies
- Lead-Free

|                        |                               |                      |
|------------------------|-------------------------------|----------------------|
| <b>V<sub>DSS</sub></b> | <b>R<sub>DS(on)</sub> max</b> | <b>I<sub>D</sub></b> |
| <b>150V</b>            | <b>0.032Ω</b>                 | <b>60A</b>           |

**Benefits**

- Low Gate-to-Drain Charge to Reduce Switching Losses
- Fully Characterized Capacitance Including Effective C<sub>OSS</sub> to Simplify Design, (See App. Note AN1001)
- Fully Characterized Avalanche Voltage and Current



**Absolute Maximum Ratings**

|   | <b>Parameter</b>                                | <b>Max.</b>            | <b>Units</b> |
|---|---|------------------------|--------------|
| I <sub>D</sub> @ T <sub>C</sub> = 25°C  | Continuous Drain Current, V <sub>GS</sub> @ 10V | 60                     | A            |
| I <sub>D</sub> @ T <sub>C</sub> = 100°C | Continuous Drain Current, V <sub>GS</sub> @ 10V | 42                     |              |
| I <sub>DM</sub>                         | Pulsed Drain Current ①                          | 250                    |              |
| P <sub>D</sub> @ T <sub>A</sub> = 25°C  | Power Dissipation                               | 2.4                    | W            |
| P <sub>D</sub> @ T <sub>C</sub> = 25°C  | Power Dissipation                               | 330                    |              |
|   | Linear Derating Factor                          | 2.2                    | W/°C         |
| V <sub>GS</sub>                         | Gate-to-Source Voltage                          | ± 30                   | V            |
| dv/dt                                   | Peak Diode Recovery dv/dt ②                     | 3.7                    | V/ns         |
| T <sub>J</sub>                          | Operating Junction and                          | -55 to + 175           | °C           |
| T <sub>STG</sub>                        | Storage Temperature Range                       |                        |              |
|   | Soldering Temperature, for 10 seconds           | 300 (1.6mm from case ) |              |
|   | Mounting torque, 6-32 or M3 screw ③             | 10 lbf•in (1.1N•m)     |              |

**Thermal Resistance**

|                  | <b>Parameter</b>                    | <b>Typ.</b> | <b>Max.</b> | <b>Units</b> |
|------------------|-------------------------------------|-------------|-------------|--------------|
| R <sub>θJC</sub> | Junction-to-Case                    | —           | 0.45        | °C/W         |
| R <sub>θCS</sub> | Case-to-Sink, Flat, Greased Surface | 0.50        | —           |              |
| R <sub>θJA</sub> | Junction-to-Ambient                 | —           | 62          |              |

Notes ① through ③ are on page 8

# IRFB61N15DPbF

International  
**IR** Rectifier

## Static @ T<sub>J</sub> = 25°C (unless otherwise specified)

|  | Parameter                            | Min. | Typ. | Max.  | Units | Conditions   |
|--|--------------------------------------|------|------|-------|-------|--|
| V <sub>(BR)DSS</sub>                   | Drain-to-Source Breakdown Voltage    | 150  | —    | —     | V     | V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA                         |
| ΔV <sub>(BR)DSS</sub> /ΔT <sub>J</sub> | Breakdown Voltage Temp. Coefficient  | —    | 0.18 | —     | V/°C  | Reference to 25°C, I <sub>D</sub> = 1mA                              |
| R <sub>DS(on)</sub>                    | Static Drain-to-Source On-Resistance | —    | —    | 0.032 | Ω     | V <sub>GS</sub> = 10V, I <sub>D</sub> = 36A ④                        |
| V <sub>GS(th)</sub>                    | Gate Threshold Voltage               | 3.0  | —    | 5.5   | V     | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA           |
| I <sub>DSS</sub>                       | Drain-to-Source Leakage Current      | —    | —    | 25    | μA    | V <sub>DS</sub> = 150V, V <sub>GS</sub> = 0V                         |
|  |                                      | —    | —    | 250   |       | V <sub>DS</sub> = 120V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 150°C |
| I <sub>GSS</sub>                       | Gate-to-Source Forward Leakage       | —    | —    | 100   | nA    | V <sub>GS</sub> = 30V  |
|  | Gate-to-Source Reverse Leakage       | —    | —    | -100  |       | V <sub>GS</sub> = -30V   |

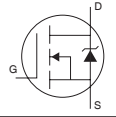
## Dynamic @ T<sub>J</sub> = 25°C (unless otherwise specified)

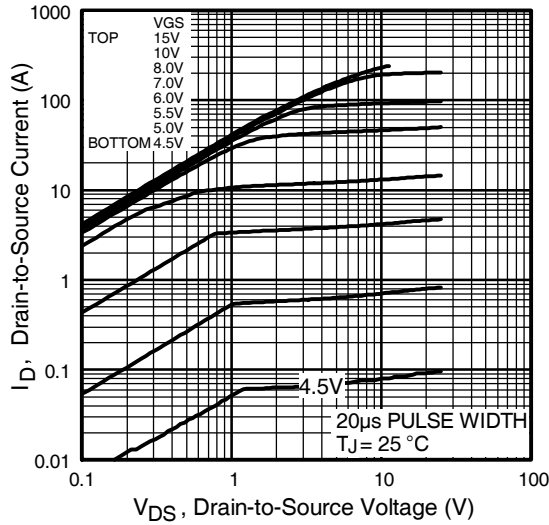
|                       | Parameter                       | Min. | Typ. | Max. | Units | Conditions   |
|-----------------------|---------------------------------|------|------|------|-------|--|
| g <sub>fs</sub>       | Forward Transconductance        | 22   | —    | —    | S     | V <sub>DS</sub> = 50V, I <sub>D</sub> = 37A              |
| Q <sub>g</sub>        | Total Gate Charge               | —    | 95   | 140  | nC    | I <sub>D</sub> = 37A                                     |
| Q <sub>gs</sub>       | Gate-to-Source Charge           | —    | 26   | 39   |       | V <sub>DS</sub> = 120V                                   |
| Q <sub>gd</sub>       | Gate-to-Drain ("Miller") Charge | —    | 45   | 68   |       | V <sub>GS</sub> = 10V,                                   |
| t <sub>d(on)</sub>    | Turn-On Delay Time              | —    | 18   | —    | ns    | V <sub>DD</sub> = 75V                                    |
| t <sub>r</sub>        | Rise Time                       | —    | 110  | —    |       | I <sub>D</sub> = 37A                                     |
| t <sub>d(off)</sub>   | Turn-Off Delay Time             | —    | 28   | —    |       | R <sub>G</sub> = 1.8Ω                                    |
| t <sub>f</sub>        | Fall Time                       | —    | 51   | —    |       | V <sub>GS</sub> = 10V ④                                  |
| C <sub>iss</sub>      | Input Capacitance               | —    | 3470 | —    | pF    | V <sub>GS</sub> = 0V                                     |
| C <sub>oss</sub>      | Output Capacitance              | —    | 690  | —    |       | V <sub>DS</sub> = 25V                                    |
| C <sub>rss</sub>      | Reverse Transfer Capacitance    | —    | 150  | —    |       | f = 1.0MHz   |
| C <sub>oss</sub>      | Output Capacitance              | —    | 4600 | —    |       | V <sub>GS</sub> = 0V, V <sub>DS</sub> = 1.0V, f = 1.0MHz |
| C <sub>oss</sub>      | Output Capacitance              | —    | 310  | —    |       | V <sub>GS</sub> = 0V, V <sub>DS</sub> = 120V, f = 1.0MHz |
| C <sub>oss eff.</sub> | Effective Output Capacitance    | —    | 580  | —    |       | V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V to 120V ⑤     |

## Avalanche Characteristics

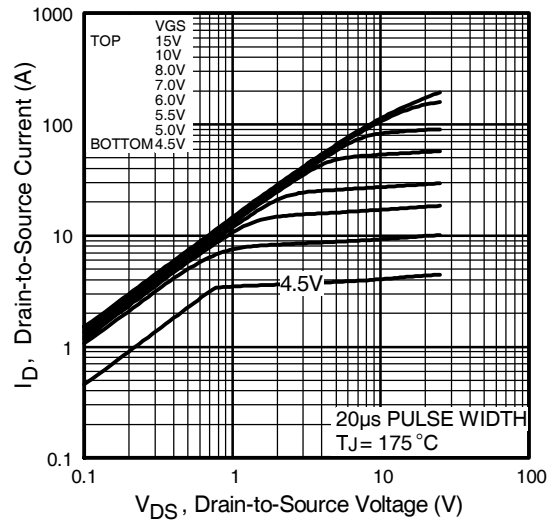
|                 | Parameter                      | Typ. | Max. | Units |
|-----------------|--------------------------------|------|------|-------|
| E <sub>AS</sub> | Single Pulse Avalanche Energy② | —    | 520  | mJ    |
| I <sub>AR</sub> | Avalanche Current①             | —    | 37   | A     |
| E <sub>AR</sub> | Repetitive Avalanche Energy①   | —    | 33   | mJ    |

## Diode Characteristics

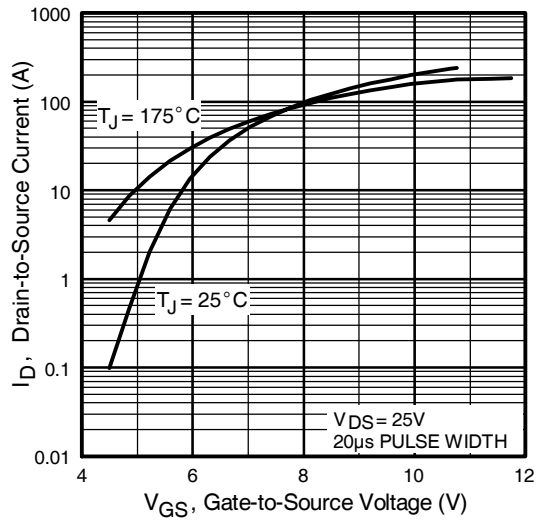
|                 | Parameter                                 | Min.   | Typ. | Max. | Units | Conditions   |
|-----------------|---|--|------|------|-------|--|
| I <sub>S</sub>  | Continuous Source Current<br>(Body Diode) | —  | —    | 60   | A     | MOSFET symbol showing the integral reverse p-n junction diode.  |
| I <sub>SM</sub> | Pulsed Source Current<br>(Body Diode) ①   | —  | —    | 250  |       |  |
| V <sub>SD</sub> | Diode Forward Voltage                     | —  | —    | 1.3  | V     | T <sub>J</sub> = 25°C, I <sub>S</sub> = 37A, V <sub>GS</sub> = 0V ④  |
| t <sub>rr</sub> | Reverse Recovery Time                     | —  | 180  | 270  | ns    | T <sub>J</sub> = 25°C, I <sub>F</sub> = 37A  |
| Q <sub>rr</sub> | Reverse Recovery Charge                   | —  | 1340 | 2010 | nC    | di/dt = 100A/μs ④  |
| t <sub>on</sub> | Forward Turn-On Time                      | Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> +L <sub>D</sub> ) |      |      |       |  |



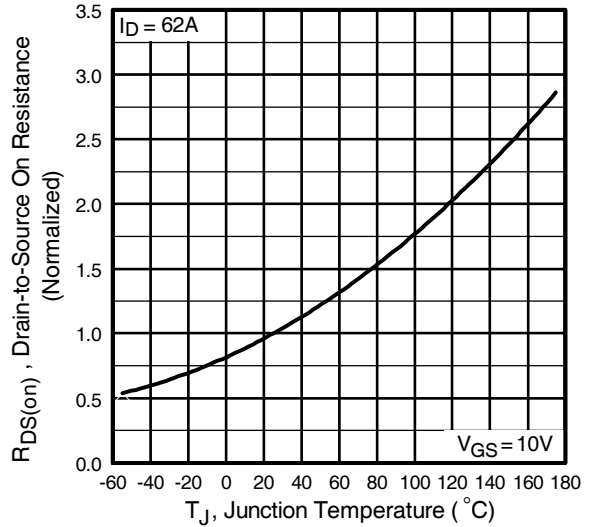
**Fig 1.** Typical Output Characteristics



**Fig 2.** Typical Output Characteristics

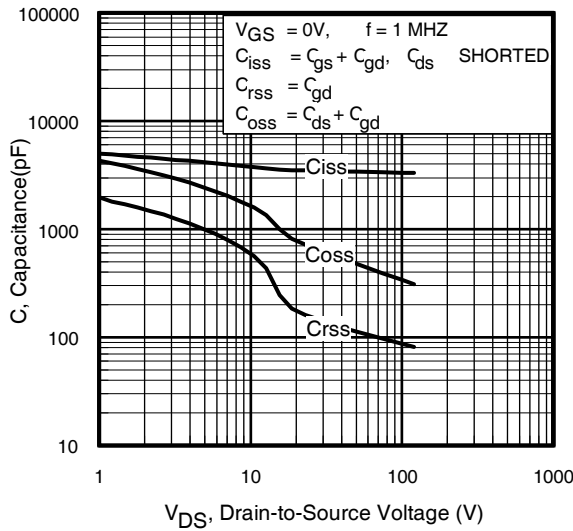


**Fig 3.** Typical Transfer Characteristics

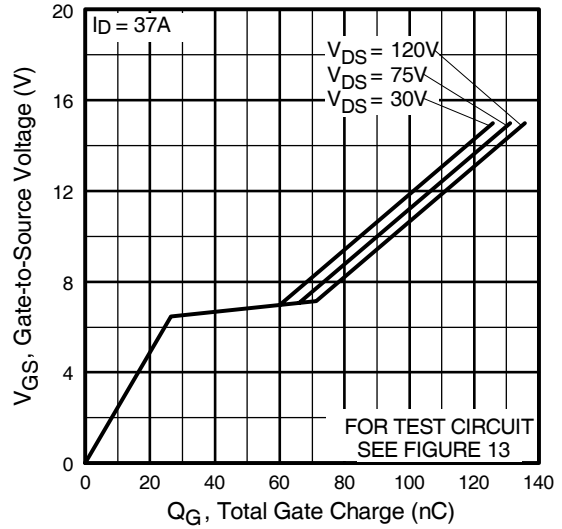


**Fig 4.** Normalized On-Resistance Vs. Temperature

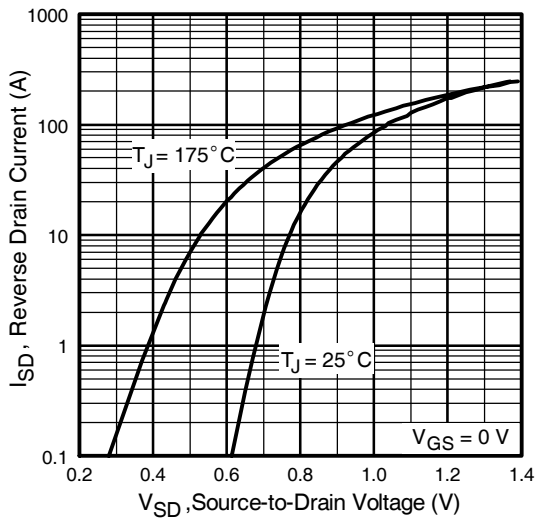
# IRFB61N15DPbF



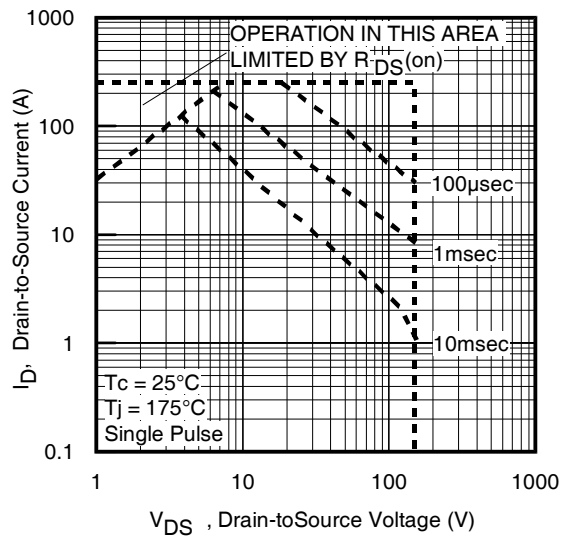
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



**Fig 7.** Typical Source-Drain Diode Forward Voltage



**Fig 8.** Maximum Safe Operating Area

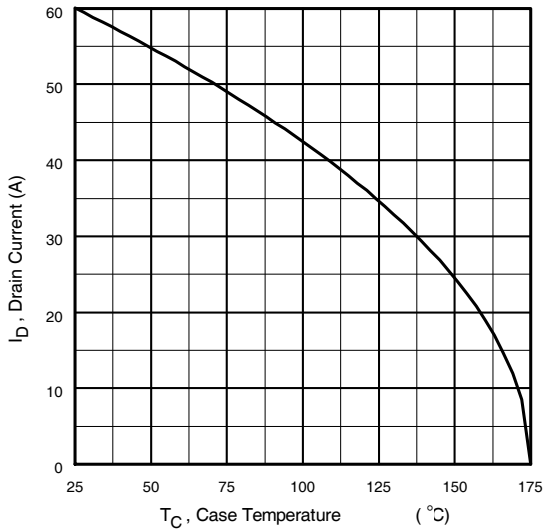


Fig 9. Maximum Drain Current Vs. Case Temperature

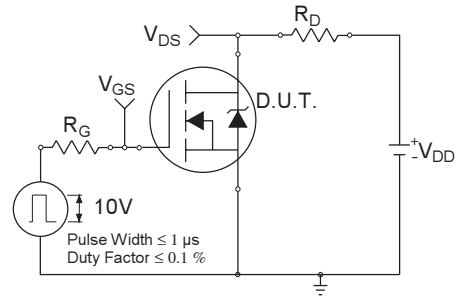


Fig 10a. Switching Time Test Circuit

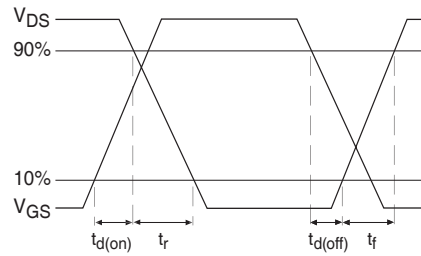


Fig 10b. Switching Time Waveforms

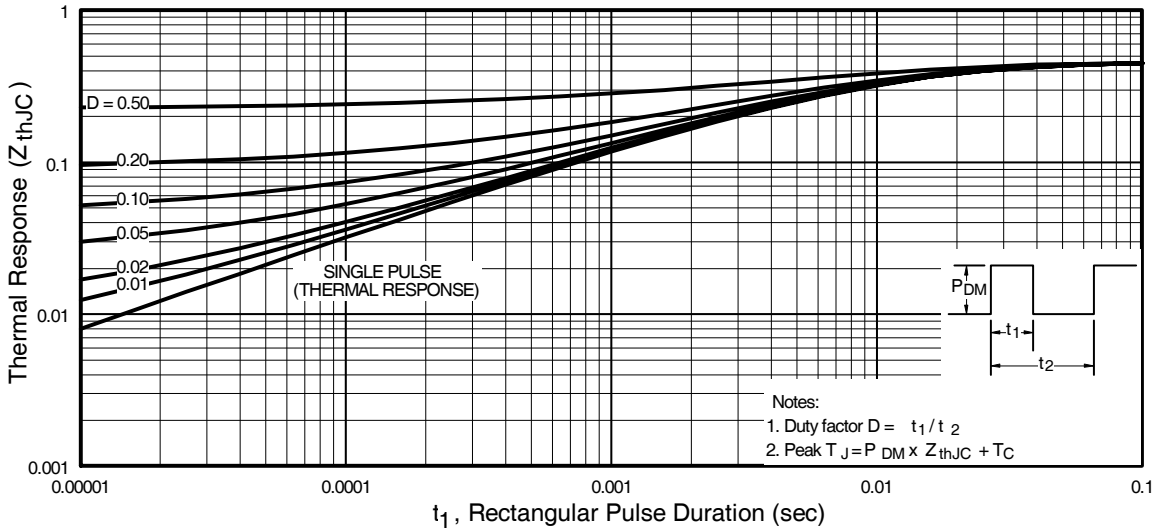
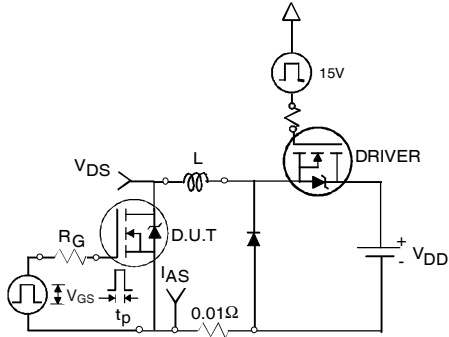


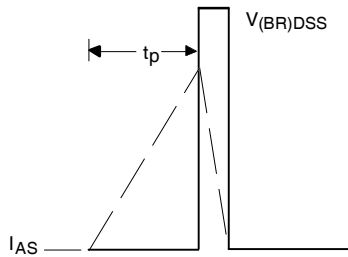
Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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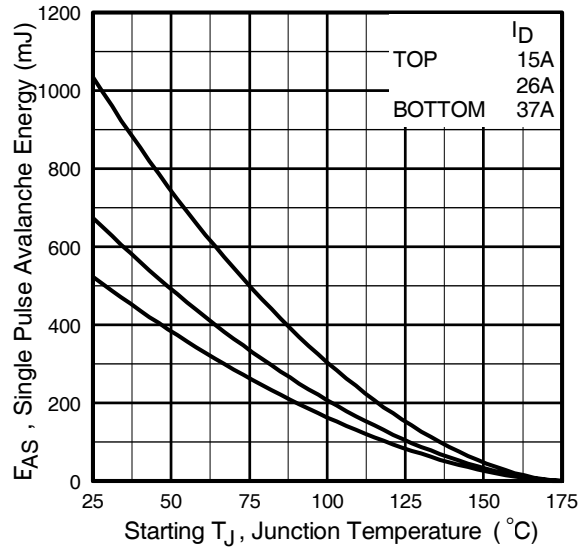
International  
**IR** Rectifier



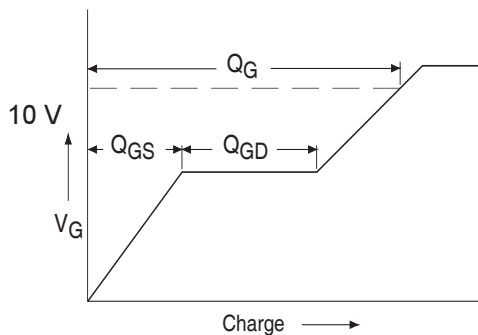
**Fig 12a.** Unclamped Inductive Test Circuit



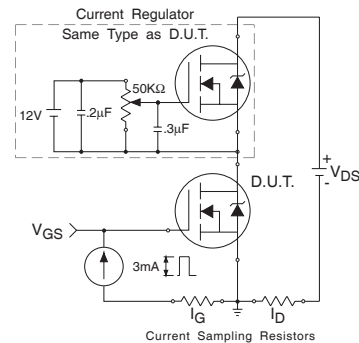
**Fig 12b.** Unclamped Inductive Waveforms



**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current

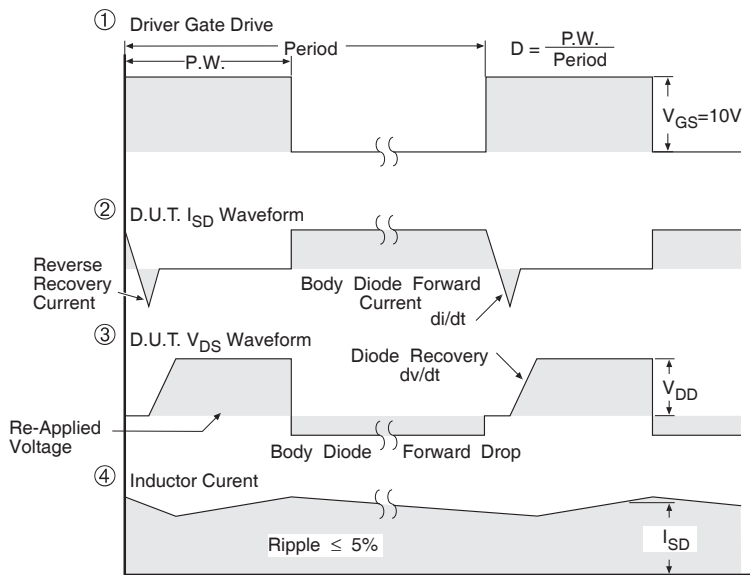
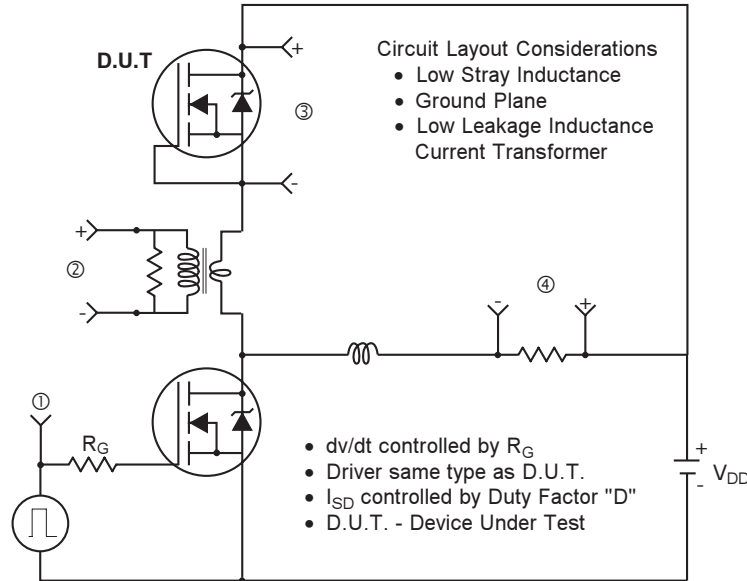


**Fig 13a.** Basic Gate Charge Waveform



**Fig 13b.** Gate Charge Test Circuit

**Peak Diode Recovery dv/dt Test Circuit**



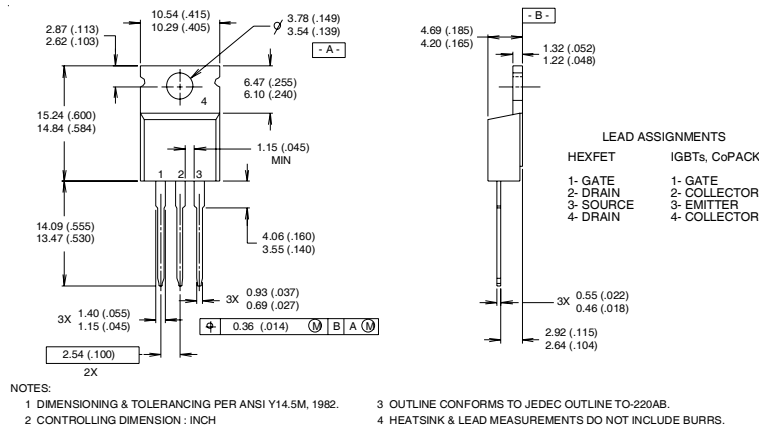
\*  $V_{GS} = 5V$  for Logic Level Devices

**Fig 14.** For N-Channel HEXFET® Power MOSFETs

# IRFB61N15DPbF

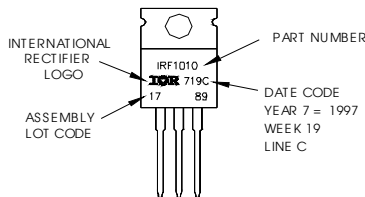


## TO-220AB Package Outline



## TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010  
 LOT CODE 1789  
 ASSEMBLED ON WW 19, 1997  
 IN THE ASSEMBLY LINE "C"  
**Note:** "P" in assembly line  
 position indicates "Lead-Free"



### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.98\text{mH}$   
 $R_G = 25\Omega$ ,  $I_{AS} = 37\text{A}$ ,  $V_{GS} = 10\text{V}$
- ③  $I_{SD} \leq 37\text{A}$ ,  $di/dt \leq 170\text{A}/\mu\text{s}$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  
 $T_J \leq 175^\circ\text{C}$
- ④ Pulse width  $\leq 400\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ⑤  $C_{OSS}$  eff. is a fixed capacitance that gives the same charging time as  $C_{OSS}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$

Data and specifications subject to change without notice.  
 This product has been designed and qualified for the Industrial market.  
 Qualification Standards can be found on IR's Web site.



**IR WORLD HEADQUARTERS:** 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105  
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Note: For the most current drawings please refer to the IR website at:  
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